

- A1**
Enter
- C**
- etching holes in the layer of TiN ~~and~~ the final layer of metal exposing portions of the interlayer dielectric, wherein metal structures are formed; [and]
removing the first layer of photoresist; [and]
removing remaining portions of the layer of TiN; and
forming a blanket layer of interlayer dielectric on the surface of the semiconductor device **A1**

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✓ Please cancel Claim 2.

Please amend Claim 3 as follows:

- A2**
3. (Once amended) The method of Claim [2] 1 further comprising:
forming a second layer of photoresist on the blanket layer of interlayer dielectric; [and]
patterning and developing the second layer of photoresist exposing portions of the blanket layer of interlayer dielectric overlying metal structures; and
etching the exposed portions of the blanket layer of interlayer dielectric overlying metal structures; and
etching the exposed portions of the blanket layer of interlayer dielectric down to the metal structures.

4. The method of Claim 3 further comprising removing the second layer of photoresist.
5. The method of Claim 1 wherein the first layer of photoresist and the layer of TiN is etched by a process utilizing fluorine containing gas chemistry at an elevated temperature.

REMARKS

Claims 1 – 5 are pending in the application and stand rejected. Applicants have amended claims 1 and 3 and have canceled Claim 2. Claims 1 and 3-5 remain in the application. Applicants request reconsideration of the rejections and an early allowance.

The Examiner rejected Claims 1 – 5 under 35 U.S.C. §102(b) as being anticipated by the Admitted Prior Art. The Examiner stated:

Referring to figures 1a – 1I, the Admitted Prior Art teaches a method of manufacturing a semiconductor device comprises: forming a final metal layer (104) over the interlayer dielectric (102), forming a TiN layer (106) over the metal layer, forming a layer of photoresist (108 over the TiN layer, patterning and developing the first layer of photoresist exposing portions of the TiN layer, etching in the layer of TiN and the final layer of metal exposing portions of the interlayer dielectric layer, removing the first layer of photoresist and the layer TiN **[It would be helpful if the Examiner would be accurate in his comments**